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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LFQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101ledfb-30

Table 1-1. List of Ordering Part Numbers

(5/12)

Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
48 pins	48-pin plastic LFQFP (7 × 7 mm, 0.5 mm pitch)	Mounted	A	R5F100GAAFB#V0, R5F100GCAFB#V0, R5F100GDAFB#V0, R5F100GEAFB#V0, R5F100GFAFB#V0, R5F100GGAFB#V0, R5F100GHAFB#V0, R5F100GJAFB#V0, R5F100GKAFB#V0, R5F100GLAFB#V0 R5F100GAAFB#X0, R5F100GCAFB#X0, R5F100GDAFB#X0, R5F100GEAFB#X0, R5F100GFAFB#X0, R5F100GGAFB#X0, R5F100GHAFB#X0, R5F100GJAFB#X0, R5F100GKAFB#X0, R5F100GLAFB#X0
		D	R5F100GADFB#V0, R5F100GCDFB#V0, R5F100GDDFB#V0, R5F100GEDFB#V0, R5F100GFDFB#V0, R5F100GGDFB#V0, R5F100GHDFB#V0, R5F100GJDFB#V0, R5F100GKDFB#V0, R5F100GLDFB#V0 R5F100GADFB#X0, R5F100GCDFB#X0, R5F100GDDFB#X0, R5F100GEDFB#X0, R5F100GFDFB#X0, R5F100GGDFB#X0, R5F100GHDFB#X0, R5F100GJDFB#X0, R5F100GKDFB#X0, R5F100GLDFB#X0	
			G	R5F100GAGFB#V0, R5F100GCGFB#V0, R5F100GDGFB#V0, R5F100GEGFB#V0, R5F100GFGFB#V0, R5F100GGGFB#V0, R5F100GHGFB#V0, R5F100GJGFB#V0 R5F100GAGFB#X0, R5F100GCGFB#X0, R5F100GDGFB#X0, R5F100GEGFB#X0, R5F100GFGFB#X0, R5F100GGGFB#X0, R5F100GHGFB#X0, R5F100GJGFB#X0
		Not mounted	A	R5F101GAAFB#V0, R5F101GCAFB#V0, R5F101GDAFB#V0, R5F101GEAFB#V0, R5F101GFAFB#V0, R5F101GGAFB#V0, R5F101GHAFB#V0, R5F101GJAFB#V0, R5F101GKAFB#V0, R5F101GLAFB#V0 R5F101GAAFB#X0, R5F101GCAFB#X0, R5F101GDAFB#X0, R5F101GEAFB#X0, R5F101GFAFB#X0, R5F101GGAFB#X0, R5F101GHAFB#X0, R5F101GJAFB#X0, R5F101GKAFB#X0, R5F101GLAFB#X0
			D	R5F101GADFB#V0, R5F101GCDFB#V0, R5F101GDDFB#V0, R5F101GEDFB#V0, R5F101GFDFB#V0, R5F101GGDFB#V0, R5F101GHDFB#V0, R5F101GJDFB#V0, R5F101GKDFB#V0, R5F101GLDFB#V0 R5F101GADFB#X0, R5F101GCDFB#X0, R5F101GDDFB#X0, R5F101GEDFB#X0, R5F101GFDFB#X0, R5F101GGDFB#X0, R5F101GHDFB#X0, R5F101GJDFB#X0, R5F101GKDFB#X0, R5F101GLDFB#X0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

Table 1-1. List of Ordering Part Numbers

(9/12)

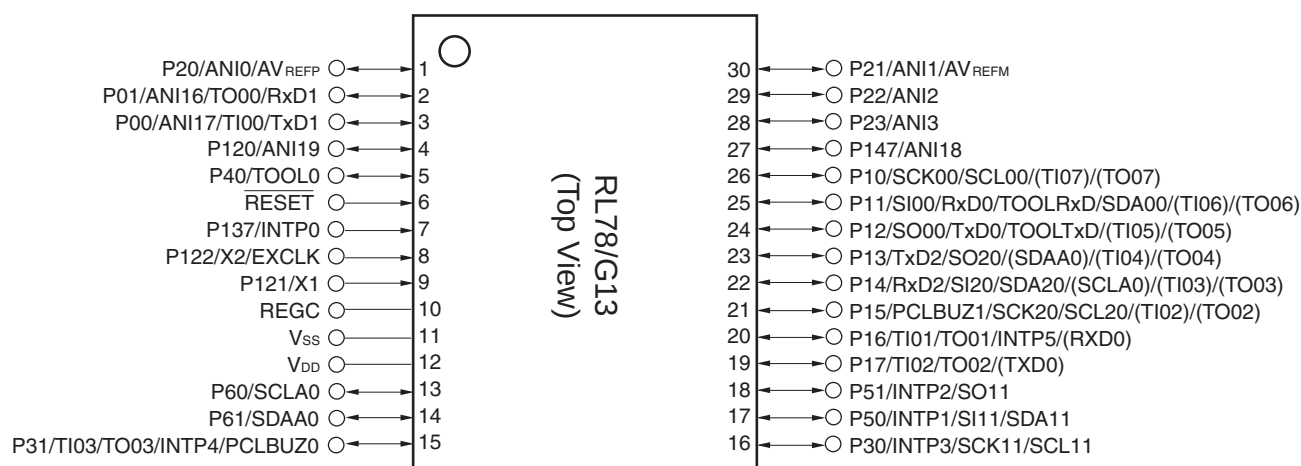
Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
64 pins	64-pin plastic LFQFP (10 × 10 mm, 0.5 mm pitch)	Mounted	A	R5F100LCAFB#V0, R5F100LDAFB#V0, R5F100LEAFB#V0, R5F100LFAFB#V0, R5F100LGAFB#V0, R5F100LHAFB#V0, R5F100LJAFB#V0, R5F100LKAFB#V0, R5F100LLAFB#V0, R5F100LCAFB#X0, R5F100LDAFB#X0, R5F100LEAFB#X0, R5F100LFAFB#X0, R5F100LGAFB#X0, R5F100LHAFB#X0, R5F100LJAFB#X0, R5F100LKAFB#X0, R5F100LLAFB#X0
			D	R5F100LCDFB#V0, R5F100LDDFB#V0, R5F100LEDFB#V0, R5F100LFDDB#V0, R5F100LGDFB#V0, R5F100LHDFB#V0, R5F100LJDFB#V0, R5F100LKDFB#V0, R5F100LLDFB#V0, R5F100LCDFB#X0, R5F100LDDFB#X0, R5F100LEDFB#X0, R5F100LFDDB#X0, R5F100LGDFB#X0, R5F100LHDFB#X0, R5F100LJDFB#X0, R5F100LKDFB#X0, R5F100LLDFB#X0
			G	R5F100LCGFB#V0, R5F100LDGFB#V0, R5F100LEGFB#V0, R5F100LFGFB#V0, R5F100LCGFB#X0, R5F100LDGFB#X0, R5F100LEGFB#X0, R5F100LFGFB#X0
				R5F100LGGFB#V0, R5F100LHGFB#V0, R5F100LJGFB#V0, R5F100LGGFB#X0, R5F100LHGFB#X0, R5F100LJGFB#X0
	64-pin plastic VFPGA (4 × 4 mm, 0.4 mm pitch)	Not mounted	A	R5F101LCAFB#V0, R5F101LDAFB#V0, R5F101LEAFB#V0, R5F101LFAFB#V0, R5F101LGAFB#V0, R5F101LHAFB#V0, R5F101LJAFB#V0, R5F101LKAFB#V0, R5F101LLAFB#V0, R5F101LCAFB#X0, R5F101LDAFB#X0, R5F101LEAFB#X0, R5F101LFAFB#X0, R5F101LGAFB#X0, R5F101LHAFB#X0, R5F101LJAFB#X0, R5F101LKAFB#X0, R5F101LLAFB#X0
			D	R5F101LCDFB#V0, R5F101LDDFB#V0, R5F101LEDFB#V0, R5F101LFDDB#V0, R5F101LGDFB#V0, R5F101LHDFB#V0, R5F101LJDFB#V0, R5F101LKDFB#V0, R5F101LLDFB#V0, R5F101LCDFB#X0, R5F101LDDFB#X0, R5F101LEDFB#X0, R5F101LFDDB#X0, R5F101LGDFB#X0, R5F101LHDFB#X0, R5F101LJDFB#X0, R5F101LKDFB#X0, R5F101LLDFB#X0
	64-pin plastic VFPGA (4 × 4 mm, 0.4 mm pitch)	Mounted	A	R5F100LCABG#U0, R5F100LDABG#U0, R5F100LEABG#U0, R5F100LFABG#U0, R5F100LGABG#U0, R5F100LHABG#U0, R5F100LJABG#U0, R5F100LCABG#W0, R5F100LDABG#W0, R5F100LEABG#W0, R5F100LFABG#W0, R5F100LGABG#W0, R5F100LHABG#W0, R5F100LJABG#W0
			G	R5F100LCGBG#U0, R5F100LDGBG#U0, R5F100LEGBG#U0, R5F100LFGBG#U0, R5F100LGGBG#U0, R5F100LHGBG#U0, R5F100LJGBG#U0, R5F100LCGBG#W0, R5F100LDGBG#W0, R5F100LEGBG#W0, R5F100LFGBG#W0, R5F100LGGBG#W0, R5F100LHGBG#W0, R5F100LJGBG#W0
	64-pin plastic VFPGA (4 × 4 mm, 0.4 mm pitch)	Not mounted	A	R5F101LCABG#U0, R5F101LDABG#U0, R5F101LEABG#U0, R5F101LFABG#U0, R5F101LGABG#U0, R5F101LHABG#U0, R5F101LJABG#U0, R5F101LCABG#W0, R5F101LDABG#W0, R5F101LEABG#W0, R5F101LFABG#W0, R5F101LGABG#W0, R5F101LHABG#W0, R5F101LJABG#W0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.4 30-pin products

- 30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)



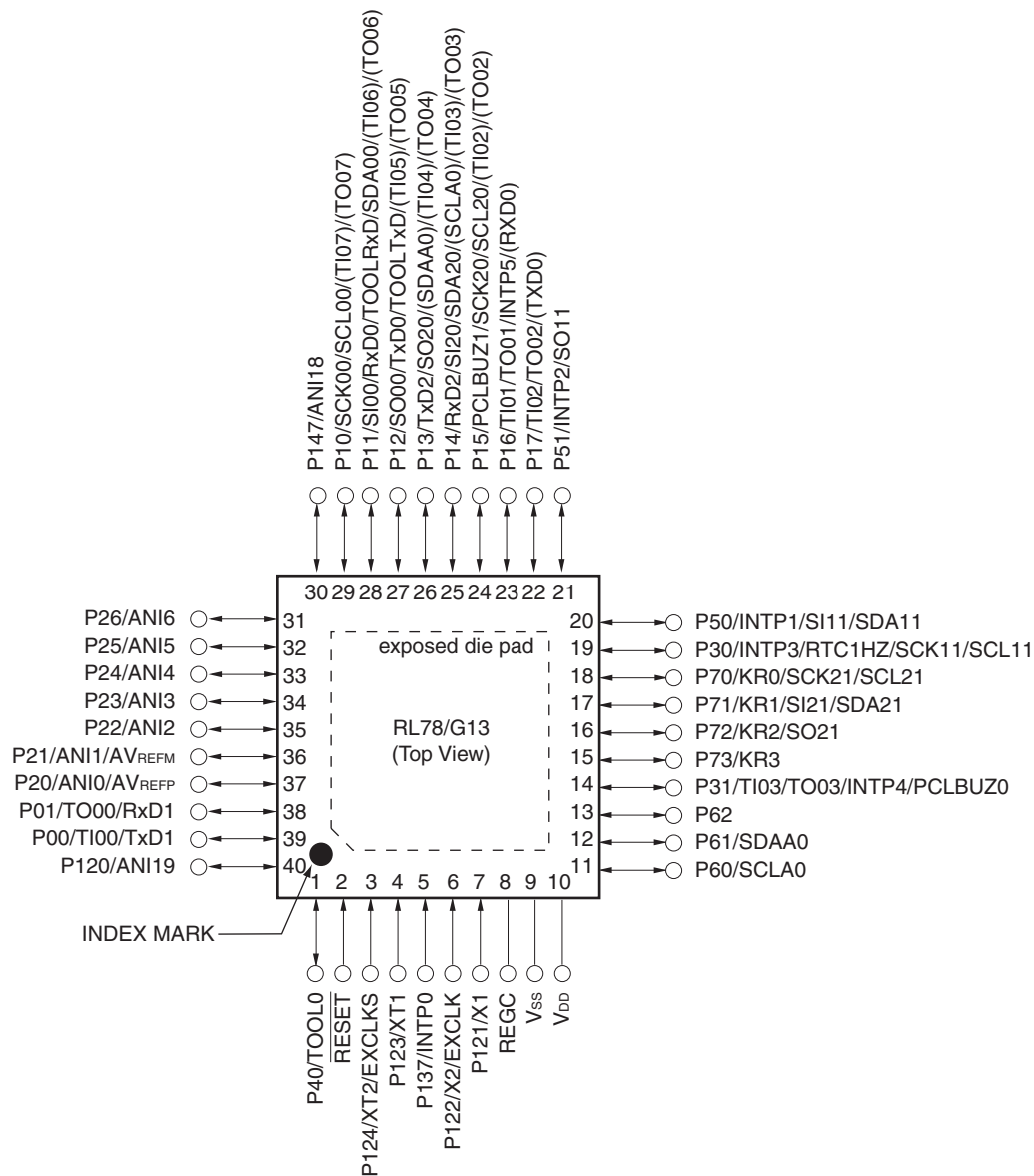
Caution Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.3.7 40-pin products

- 40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)



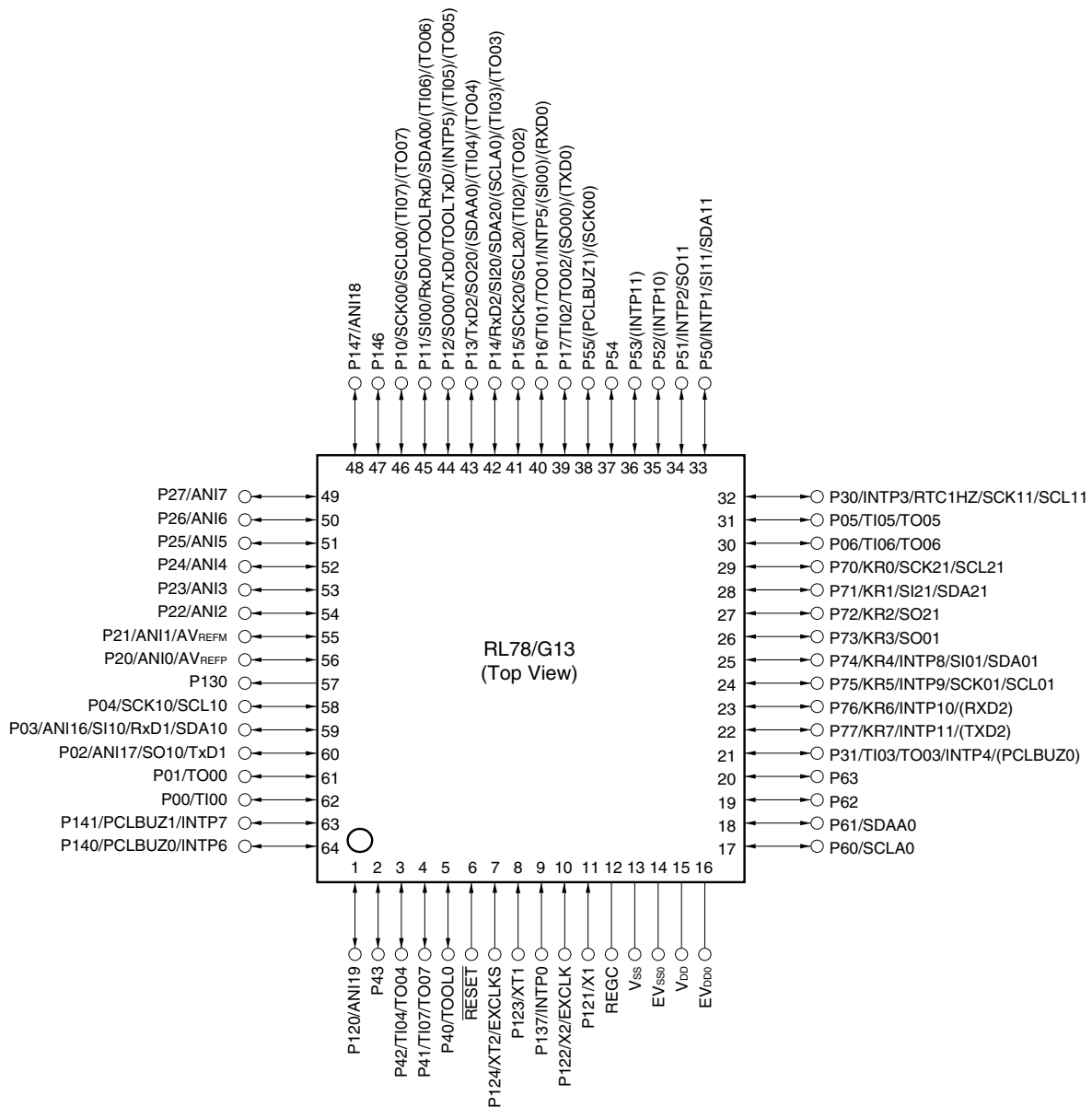
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.
- It is recommended to connect an exposed die pad to Vss.

1.3.11 64-pin products

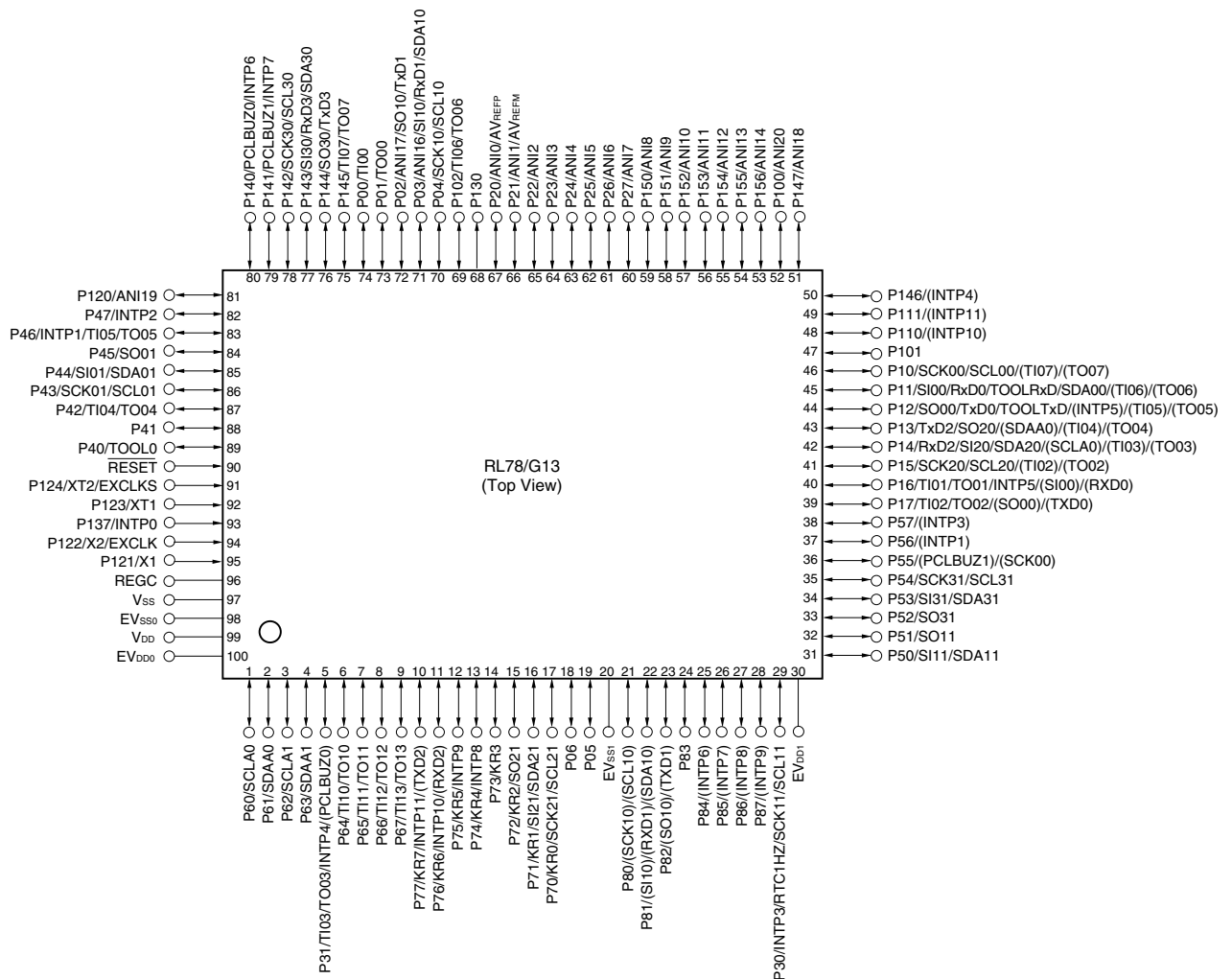
- 64-pin plastic LQFP (12 × 12 mm, 0.65 mm pitch)
- 64-pin plastic LFQFP (10 × 10 mm, 0.5 mm pitch)



- Cautions**
1. Make EV_{SS0} pin the same potential as V_{SS} pin.
 2. Make V_{DD} pin the potential that is higher than EV_{DD0} pin.
 3. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μ F).

- Remarks**
1. For pin identification, see 1.4 Pin Identification.
 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD} and EV_{DD0} pins and connect the V_{SS} and EV_{SS0} pins to separate ground lines.
 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

- 100-pin plastic LQFP (14 × 20 mm, 0.65 mm pitch)



- Cautions**
1. Make EV_{SS0}, EV_{SS1} pins the same potential as V_{SS} pin.
 2. Make V_{DD} pin the potential that is higher than EV_{DD0}, EV_{DD1} pins (EV_{DD0} = EV_{DD1}).
 3. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF).

- Remarks**
1. For pin identification, see 1.4 Pin Identification.
 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD}, EV_{DD0} and EV_{DD1} pins and connect the V_{SS}, EV_{SS0} and EV_{SS1} pins to separate ground lines.
 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

2. ELECTRICAL SPECIFICATIONS ($T_A = -40$ to $+85^\circ\text{C}$)

This chapter describes the following electrical specifications.

Target products A: Consumer applications $T_A = -40$ to $+85^\circ\text{C}$

R5F100xxAxx, R5F101xxAxx

D: Industrial applications $T_A = -40$ to $+85^\circ\text{C}$

R5F100xxDxx, R5F101xxDxx

G: Industrial applications when $T_A = -40$ to $+105^\circ\text{C}$ products is used in the range of $T_A = -40$ to $+85^\circ\text{C}$

R5F100xxGxx

- Cautions**
1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 2. With products not provided with an EV_{DD0} , EV_{DD1} , EV_{SS0} , or EV_{SS1} pin, replace EV_{DD0} and EV_{DD1} with V_{DD} , or replace EV_{SS0} and EV_{SS1} with V_{SS} .
 3. The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 Functions for each product.

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products

(T_A = -40 to +85°C, 1.6 V ≤ E_{VDD0} ≤ V_{DD} ≤ 5.5 V, V_{SS} = E_{VSS0} = 0 V) (2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit	
Supply current Note 1	I _{DD2} Note 2	HALT mode	HS (high-speed main) mode Note 7	f _{IH} = 32 MHz ^{Note 4}	V _{DD} = 5.0 V		0.54	1.63	mA	
					V _{DD} = 3.0 V		0.54	1.63	mA	
				f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		0.44	1.28	mA	
					V _{DD} = 3.0 V		0.44	1.28	mA	
				f _{IH} = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		0.40	1.00	mA	
					V _{DD} = 3.0 V		0.40	1.00	mA	
			LS (low-speed main) mode Note 7	f _{IH} = 8 MHz ^{Note 4}	V _{DD} = 3.0 V		260	530	μA	
					V _{DD} = 2.0 V		260	530	μA	
			LV (low-voltage main) mode Note 7	f _{IH} = 4 MHz ^{Note 4}	V _{DD} = 3.0 V		420	640	μA	
					V _{DD} = 2.0 V		420	640	μA	
			HS (high-speed main) mode Note 7	f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		0.28	1.00	mA	
					Resonator connection		0.45	1.17	mA	
				f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		0.28	1.00	mA	
					Resonator connection		0.45	1.17	mA	
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		0.19	0.60	mA	
					Resonator connection		0.26	0.67	mA	
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		0.19	0.60	mA	
					Resonator connection		0.26	0.67	mA	
			LS (low-speed main) mode Note 7	f _{MX} = 8 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		95	330	μA	
					Resonator connection		145	380	μA	
				f _{MX} = 8 MHz ^{Note 3} , V _{DD} = 2.0 V	Square wave input		95	330	μA	
					Resonator connection		145	380	μA	
			Subsystem clock operation	f _{SUB} = 32.768 kHz ^{Note 5} T _A = −40°C	Square wave input		0.25	0.57	μA	
					Resonator connection		0.44	0.76	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +25°C	Square wave input		0.30	0.57	μA	
					Resonator connection		0.49	0.76	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +50°C	Square wave input		0.37	1.17	μA	
					Resonator connection		0.56	1.36	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +70°C	Square wave input		0.53	1.97	μA	
					Resonator connection		0.72	2.16	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +85°C	Square wave input		0.82	3.37	μA	
					Resonator connection		1.01	3.56	μA	
	I _{DD3} Note 6	STOP mode Note 8	T _A = −40°C					0.18	0.50	μA
			T _A = +25°C					0.23	0.50	μA
			T _A = +50°C					0.30	1.10	μA
			T _A = +70°C					0.46	1.90	μA
			T _A = +85°C					0.75	3.30	μA

(Notes and Remarks are listed on the next page.)

- Notes**
1. Total current flowing into V_{DD} , EV_{DD0} , and EV_{DD1} , including the input leakage current flowing when the level of the input pin is fixed to V_{DD} , EV_{DD0} , and EV_{DD1} , or V_{SS} , EV_{SS0} , and EV_{SS1} . The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 2. During HALT instruction execution by flash memory.
 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 4. When high-speed system clock and subsystem clock are stopped.
 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When $RTCLPC = 1$ and setting ultra-low current consumption ($AMPHS1 = 1$). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 32 MHz
 $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 16 MHz
 - LS (low-speed main) mode: $1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 8 MHz
 - LV (low-voltage main) mode: $1.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 4 MHz
 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.

- Remarks 1.** f_{MX} : High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- 2.** f_{IH} : High-speed on-chip oscillator clock frequency
- 3.** f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)
- 4.** Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^{\circ}\text{C}$

2.4 AC Characteristics

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T _{CY}	Main system clock (f _{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125	1	μs
				2.4 V ≤ V _{DD} < 2.7 V	0.0625	1	μs
			LS (low-speed main) mode	1.8 V ≤ V _{DD} ≤ 5.5 V	0.125	1	μs
			LV (low-voltage main) mode	1.6 V ≤ V _{DD} ≤ 5.5 V	0.25	1	μs
		Subsystem clock (f _{SUB}) operation		1.8 V ≤ V _{DD} ≤ 5.5 V	28.5	30.5	31.3 μs
		In the self programming mode	HS (high-speed main) mode	2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125	1	μs
				2.4 V ≤ V _{DD} < 2.7 V	0.0625	1	μs
			LS (low-speed main) mode	1.8 V ≤ V _{DD} ≤ 5.5 V	0.125	1	μs
			LV (low-voltage main) mode	1.8 V ≤ V _{DD} ≤ 5.5 V	0.25	1	μs
External system clock frequency	f _{EX}	2.7 V ≤ V _{DD} ≤ 5.5 V		1.0		20.0	MHz
		2.4 V ≤ V _{DD} < 2.7 V		1.0		16.0	MHz
		1.8 V ≤ V _{DD} < 2.4 V		1.0		8.0	MHz
		1.6 V ≤ V _{DD} < 1.8 V		1.0		4.0	MHz
	f _{EXS}			32		35	kHz
External system clock input high-level width, low-level width	t _{EXH} , t _{EXL}	2.7 V ≤ V _{DD} ≤ 5.5 V		24			ns
		2.4 V ≤ V _{DD} < 2.7 V		30			ns
		1.8 V ≤ V _{DD} < 2.4 V		60			ns
		1.6 V ≤ V _{DD} < 1.8 V		120			ns
	t _{EXHS} , t _{EXLS}			13.7			μs
Ti00 to Ti07, Ti10 to Ti17 input high-level width, low-level width	t _{TIH} , t _{TIL}			1/f _{MCK} +10			ns ^{Note}
TO00 to TO07, TO10 to TO17 output frequency	f _{TO}	HS (high-speed main) mode		4.0 V ≤ EV _{DD0} ≤ 5.5 V		16	MHz
				2.7 V ≤ EV _{DD0} < 4.0 V		8	MHz
				1.8 V ≤ EV _{DD0} < 2.7 V		4	MHz
				1.6 V ≤ EV _{DD0} < 1.8 V		2	MHz
		LS (low-speed main) mode		1.8 V ≤ EV _{DD0} ≤ 5.5 V		4	MHz
				1.6 V ≤ EV _{DD0} < 1.8 V		2	MHz
		LV (low-voltage main) mode		1.6 V ≤ EV _{DD0} ≤ 5.5 V		2	MHz
PCLBUZ0, PCLBUZ1 output frequency	f _{PCL}	HS (high-speed main) mode		4.0 V ≤ EV _{DD0} ≤ 5.5 V		16	MHz
				2.7 V ≤ EV _{DD0} < 4.0 V		8	MHz
				1.8 V ≤ EV _{DD0} < 2.7 V		4	MHz
				1.6 V ≤ EV _{DD0} < 1.8 V		2	MHz
		LS (low-speed main) mode		1.8 V ≤ EV _{DD0} ≤ 5.5 V		4	MHz
				1.6 V ≤ EV _{DD0} < 1.8 V		2	MHz
		LV (low-voltage main) mode		1.8 V ≤ EV _{DD0} ≤ 5.5 V		4	MHz
				1.6 V ≤ EV _{DD0} < 1.8 V		2	MHz
Interrupt input high-level width, low-level width	t _{INTH} , t _{INTL}	INTP0	1.6 V ≤ V _{DD} ≤ 5.5 V	1			μs
		INTP1 to INTP11	1.6 V ≤ EV _{DD0} ≤ 5.5 V	1			μs
Key interrupt input low-level width	t _{KR}	KR0 to KR7	1.8 V ≤ EV _{DD0} ≤ 5.5 V	250			ns
			1.6 V ≤ EV _{DD0} < 1.8 V	1			μs
RESET low-level width	t _{RSL}			10			μs

(Note and Remark are listed on the next page.)

Note The following conditions are required for low voltage interface when $E_{VDD0} < V_{DD}$

$1.8\text{ V} \leq E_{VDD0} < 2.7\text{ V}$: MIN. 125 ns

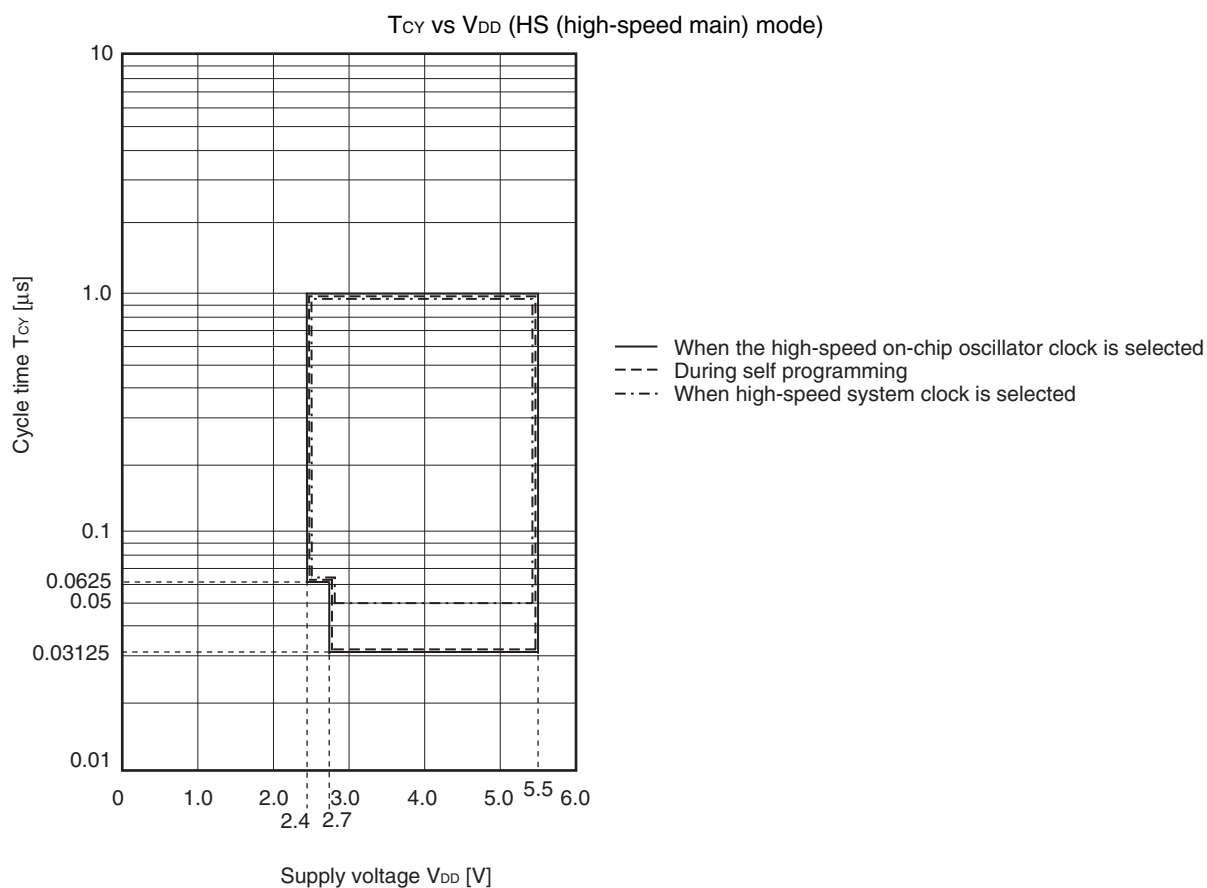
$1.6\text{ V} \leq E_{VDD0} < 1.8\text{ V}$: MIN. 250 ns

Remark f_{MCK} : Timer array unit operation clock frequency

(Operation clock to be set by the CKSmn0, CKSmn1 bits of timer mode register mn (TMRmn).

m: Unit number ($m = 0, 1$), n: Channel number ($n = 0$ to 7))

Minimum Instruction Execution Time during Main System Clock Operation



2.6.2 Temperature sensor/internal reference voltage characteristics

(T_A = -40 to $+85^\circ\text{C}$, $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$, HS (high-speed main) mode)

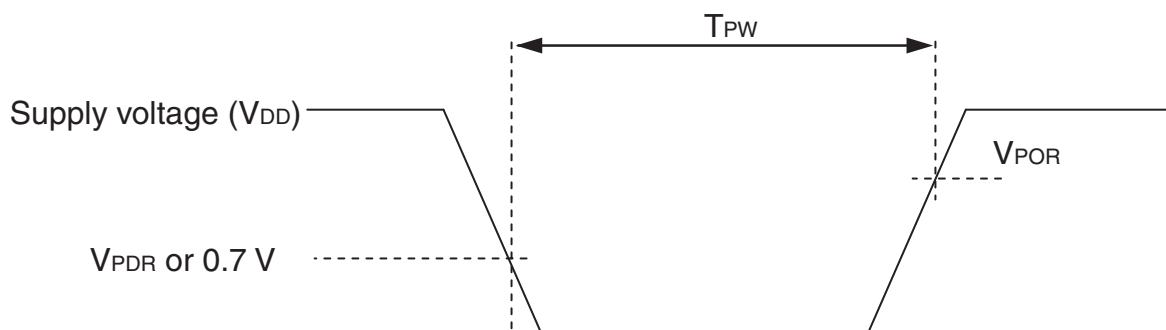
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V_{TMPS25}	Setting ADS register = 80H, $T_A = +25^\circ\text{C}$		1.05		V
Internal reference voltage	V_{BGR}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	F_{VTMPS}	Temperature sensor that depends on the temperature		-3.6		mV/ $^\circ\text{C}$
Operation stabilization wait time	t_{AMP}		5			μs

2.6.3 POR circuit characteristics

(T_A = -40 to $+85^\circ\text{C}$, $V_{SS} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V_{POR}	Power supply rise time	1.47	1.51	1.55	V
	V_{PDR}	Power supply fall time	1.46	1.50	1.54	V
Minimum pulse width ^{Note}	T_{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR} . This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



2.8 Flash Memory Programming Characteristics

(T_A = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	f _{CLK}	1.8 V ≤ V _{DD} ≤ 5.5 V	1		32	MHz
Number of code flash rewrites Notes 1, 2, 3	C _{erwr}	Retained for 20 years T _A = 85°C	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 years T _A = 25°C		1,000,000		
		Retained for 5 years T _A = 85°C	100,000			
		Retained for 20 years T _A = 85°C	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite.

The retaining years are until next rewrite after the rewrite.

2. When using flash memory programmer and Renesas Electronics self programming library

3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0\text{ V}$) (4/5)

Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output voltage, high	V_{OH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $\text{I}_{\text{OH1}} = -3.0\text{ mA}$	$\text{EV}_{\text{DD0}} - 0.7$		V
			$2.7\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $\text{I}_{\text{OH1}} = -2.0\text{ mA}$	$\text{EV}_{\text{DD0}} - 0.6$		V
			$2.4\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $\text{I}_{\text{OH1}} = -1.5\text{ mA}$	$\text{EV}_{\text{DD0}} - 0.5$		V
	V_{OH2}	P20 to P27, P150 to P156	$2.4\text{ V} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{I}_{\text{OH2}} = -100\text{ }\mu\text{A}$	$\text{V}_{\text{DD}} - 0.5$		V
Output voltage, low	V_{OL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $\text{I}_{\text{OL1}} = 8.5\text{ mA}$		0.7	V
			$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $\text{I}_{\text{OL1}} = 3.0\text{ mA}$		0.6	V
			$2.7\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $\text{I}_{\text{OL1}} = 1.5\text{ mA}$		0.4	V
			$2.4\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $\text{I}_{\text{OL1}} = 0.6\text{ mA}$		0.4	V
	V_{OL2}	P20 to P27, P150 to P156	$2.4\text{ V} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{I}_{\text{OL2}} = 400\text{ }\mu\text{A}$		0.4	V
	V_{OL3}	P60 to P63	$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $\text{I}_{\text{OL3}} = 15.0\text{ mA}$		2.0	V
			$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $\text{I}_{\text{OL3}} = 5.0\text{ mA}$		0.4	V
			$2.7\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $\text{I}_{\text{OL3}} = 3.0\text{ mA}$		0.4	V
			$2.4\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $\text{I}_{\text{OL3}} = 2.0\text{ mA}$		0.4	V

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0\text{ V}$) (1/2)**

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I _{DD1}	Operating mode	HS (high-speed main) mode Note 5	$f_{\text{IH}} = 32\text{ MHz}$ Note 3	Basic operation	$\text{V}_{\text{DD}} = 5.0\text{ V}$		2.3		mA
						$\text{V}_{\text{DD}} = 3.0\text{ V}$		2.3		mA
					Normal operation	$\text{V}_{\text{DD}} = 5.0\text{ V}$		5.2	9.2	mA
						$\text{V}_{\text{DD}} = 3.0\text{ V}$		5.2	9.2	mA
				$f_{\text{IH}} = 24\text{ MHz}$ Note 3	Normal operation	$\text{V}_{\text{DD}} = 5.0\text{ V}$		4.1	7.0	mA
						$\text{V}_{\text{DD}} = 3.0\text{ V}$		4.1	7.0	mA
				$f_{\text{IH}} = 16\text{ MHz}$ Note 3	Normal operation	$\text{V}_{\text{DD}} = 5.0\text{ V}$		3.0	5.0	mA
						$\text{V}_{\text{DD}} = 3.0\text{ V}$		3.0	5.0	mA
			HS (high-speed main) mode Note 5	$f_{\text{MX}} = 20\text{ MHz}$ Note 2, $\text{V}_{\text{DD}} = 5.0\text{ V}$	Normal operation	Square wave input		3.4	5.9	mA
						Resonator connection		3.6	6.0	mA
				$f_{\text{MX}} = 20\text{ MHz}$ Note 2, $\text{V}_{\text{DD}} = 3.0\text{ V}$	Normal operation	Square wave input		3.4	5.9	mA
						Resonator connection		3.6	6.0	mA
				$f_{\text{MX}} = 10\text{ MHz}$ Note 2, $\text{V}_{\text{DD}} = 5.0\text{ V}$	Normal operation	Square wave input		2.1	3.5	mA
						Resonator connection		2.1	3.5	mA
				$f_{\text{MX}} = 10\text{ MHz}$ Note 2, $\text{V}_{\text{DD}} = 3.0\text{ V}$	Normal operation	Square wave input		2.1	3.5	mA
						Resonator connection		2.1	3.5	mA
		Subsystem clock operation		$f_{\text{SUB}} = 32.768\text{ kHz}$ Note 4 $T_A = -40^\circ\text{C}$	Normal operation	Square wave input		4.8	5.9	μA
						Resonator connection		4.9	6.0	μA
				$f_{\text{SUB}} = 32.768\text{ kHz}$ Note 4 $T_A = +25^\circ\text{C}$	Normal operation	Square wave input		4.9	5.9	μA
						Resonator connection		5.0	6.0	μA
				$f_{\text{SUB}} = 32.768\text{ kHz}$ Note 4 $T_A = +50^\circ\text{C}$	Normal operation	Square wave input		5.0	7.6	μA
						Resonator connection		5.1	7.7	μA
				$f_{\text{SUB}} = 32.768\text{ kHz}$ Note 4 $T_A = +70^\circ\text{C}$	Normal operation	Square wave input		5.2	9.3	μA
						Resonator connection		5.3	9.4	μA
				$f_{\text{SUB}} = 32.768\text{ kHz}$ Note 4 $T_A = +85^\circ\text{C}$	Normal operation	Square wave input		5.7	13.3	μA
						Resonator connection		5.8	13.4	μA
				$f_{\text{SUB}} = 32.768\text{ kHz}$ Note 4 $T_A = +105^\circ\text{C}$	Normal operation	Square wave input		10.0	46.0	μA
						Resonator connection		10.0	46.0	μA

(Notes and Remarks are listed on the next page.)

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0\text{ V}$)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCKp cycle time	$t_{\text{KCY}1}$	$t_{\text{KCY}1} \geq 4/f_{\text{CLK}}$			
		$2.7\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$	250		ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$	500		ns
SCKp high-/low-level width	$t_{\text{KH}1},$ $t_{\text{KL}1}$	$4.0\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$	$t_{\text{KCY}1}/2 - 24$		ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$	$t_{\text{KCY}1}/2 - 36$		ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$	$t_{\text{KCY}1}/2 - 76$		ns
Slp setup time (to SCKp $\uparrow$) ^{Note 1}	$t_{\text{SIK}1}$	$4.0\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$	66		ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$	66		ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$	113		ns
Slp hold time (from SCKp $\uparrow$) ^{Note 2}	$t_{\text{KSI}1}$		38		ns
Delay time from SCKp $\downarrow$ to SOp output ^{Note 3}	$t_{\text{KSO}1}$	$C = 30\text{ pF}$ ^{Note 4}		50	ns

- Notes**
1. When $\text{DAP}_{\text{mn}} = 0$ and $\text{CKP}_{\text{mn}} = 0$, or $\text{DAP}_{\text{mn}} = 1$ and $\text{CKP}_{\text{mn}} = 1$. The Slp setup time becomes “to SCKp $\downarrow$ ” when $\text{DAP}_{\text{mn}} = 0$ and $\text{CKP}_{\text{mn}} = 1$, or $\text{DAP}_{\text{mn}} = 1$ and $\text{CKP}_{\text{mn}} = 0$.
 2. When $\text{DAP}_{\text{mn}} = 0$ and $\text{CKP}_{\text{mn}} = 0$, or $\text{DAP}_{\text{mn}} = 1$ and $\text{CKP}_{\text{mn}} = 1$. The Slp hold time becomes “from SCKp $\downarrow$ ” when $\text{DAP}_{\text{mn}} = 0$ and $\text{CKP}_{\text{mn}} = 1$, or $\text{DAP}_{\text{mn}} = 1$ and $\text{CKP}_{\text{mn}} = 0$.
 3. When $\text{DAP}_{\text{mn}} = 0$ and $\text{CKP}_{\text{mn}} = 0$, or $\text{DAP}_{\text{mn}} = 1$ and $\text{CKP}_{\text{mn}} = 1$. The delay time to SOp output becomes “from SCKp $\uparrow$ ” when $\text{DAP}_{\text{mn}} = 0$ and $\text{CKP}_{\text{mn}} = 1$, or $\text{DAP}_{\text{mn}} = 1$ and $\text{CKP}_{\text{mn}} = 0$.
 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the Slp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- Remarks**
1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),
g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)
 2. f_{MCK} : Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0\text{ V}$)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{\text{KCY1}} \geq 4/f_{\text{CLK}}$	$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 1.4\text{ k}\Omega$	600		ns
			$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$	1000		ns
			$2.4\text{ V} \leq \text{EV}_{\text{DD0}} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 5.5\text{ k}\Omega$	2300		ns
SCKp high-level width	t_{KH1}		$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 1.4\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 150$		ns
			$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 340$		ns
			$2.4\text{ V} \leq \text{EV}_{\text{DD0}} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 5.5\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 916$		ns
SCKp low-level width	t_{KL1}		$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 1.4\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 24$		ns
			$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 36$		ns
			$2.4\text{ V} \leq \text{EV}_{\text{DD0}} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 5.5\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 100$		ns

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

(2) When reference voltage (+) = $AV_{REFP}/ANI0$ ($ADREFP1 = 0$, $ADREFP0 = 1$), reference voltage (–) = $AV_{REFM}/ANI1$ ($ADREFM = 1$), target pin : ANI16 to ANI26

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $2.4\text{ V} \leq AV_{REFP} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$, Reference voltage (+) = AV_{REFP} , Reference voltage (–) = $AV_{REFM} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$	1.2	± 5.0	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin : ANI16 to ANI26	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125	39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.1875	39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17	39	μs
Zero-scale error ^{Notes 1, 2}	E_{ZS}	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 0.35	%FSR
Full-scale error ^{Notes 1, 2}	E_{FS}	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 0.35	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 3.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 2.0	LSB
Analog input voltage	V_{AIN}	ANI16 to ANI26	0		AV_{REFP} and EV_{DD0}	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when $AV_{REFP} = V_{DD}$.

Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

4. When $AV_{REFP} < EV_{DD0} \leq V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

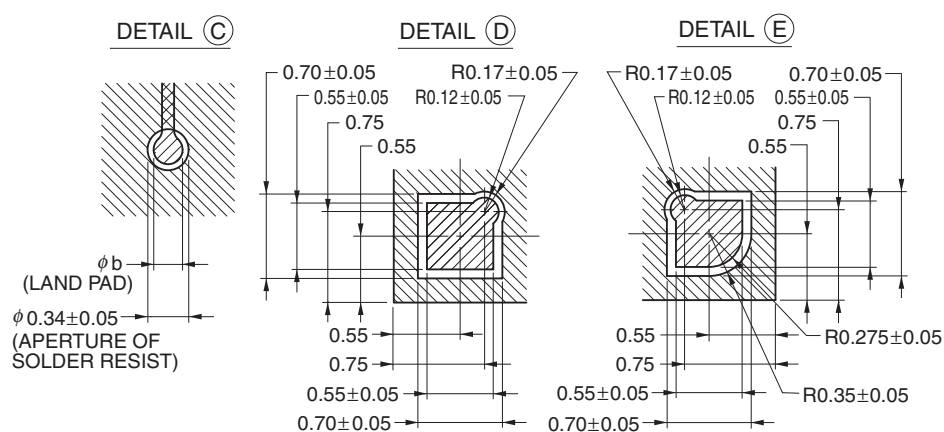
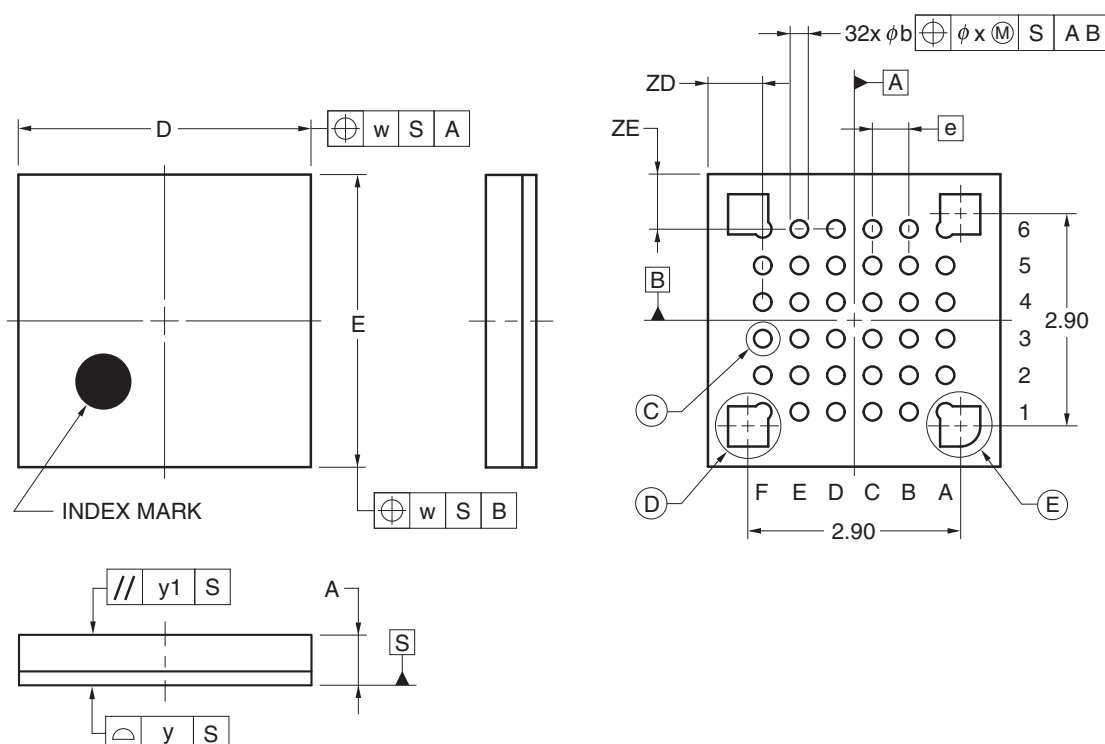
Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when $AV_{REFP} = V_{DD}$.

Integral linearity error/ Differential linearity error: Add ± 2.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

4.6 36-pin Products

R5F100CAALA, R5F100CCALA, R5F100CDALA, R5F100CEALA, R5F100CFALA, R5F100CGALA
 R5F101CAALA, R5F101CCALA, R5F101CDALA, R5F101CEALA, R5F101CFALA, R5F101CGALA
 R5F100CAGLA, R5F100CCGLA, R5F100CDGLA, R5F100CEGLA, R5F100CFGLA, R5F100CGGLA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA36-4x4-0.50	PWLG0036KA-A	P36FC-50-AA4-2	0.023

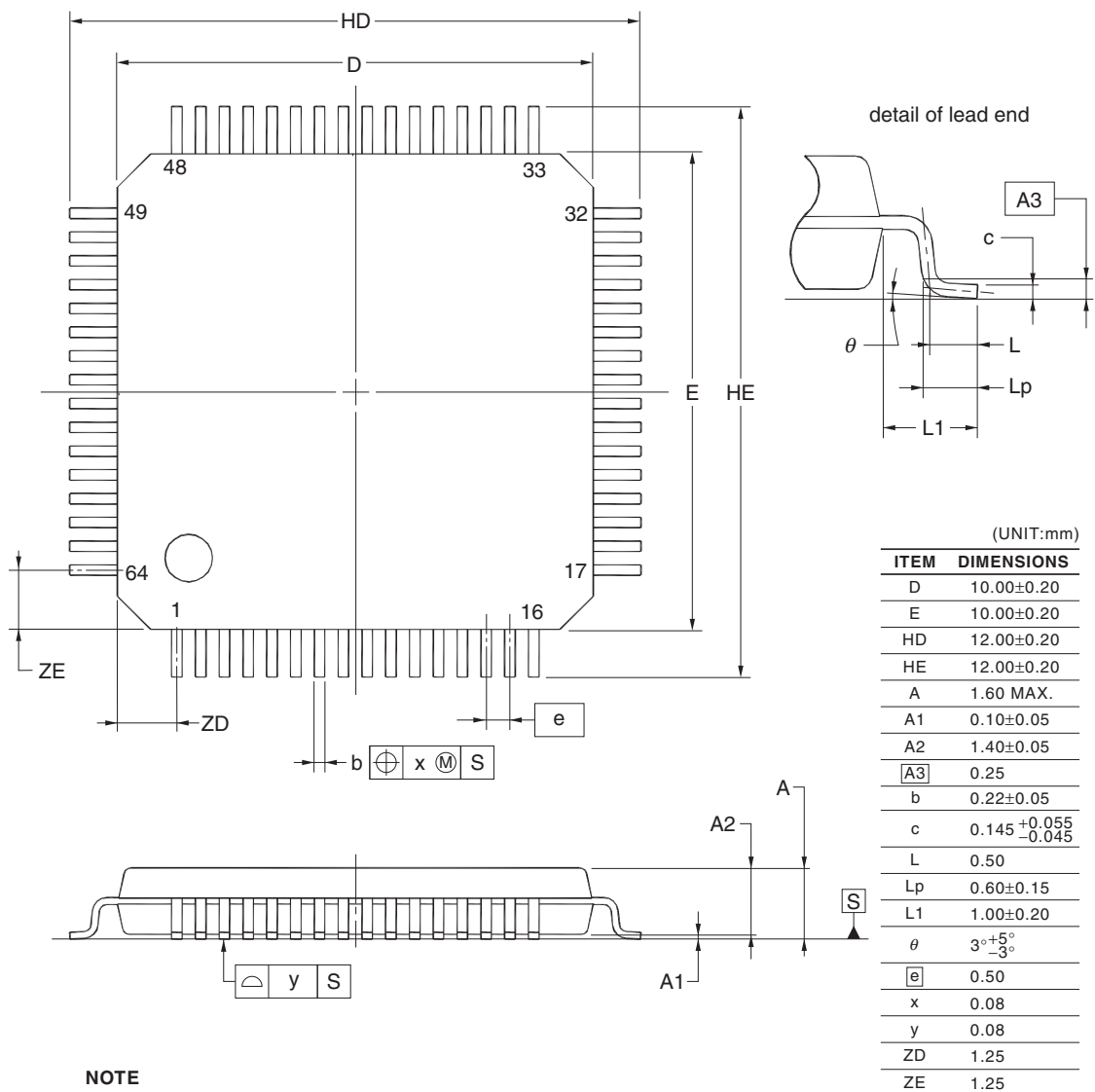


(UNIT:mm)	
ITEM	DIMENSIONS
D	4.00±0.10
E	4.00±0.10
w	0.20
e	0.50
A	0.69±0.07
b	0.24±0.05
x	0.05
y	0.08
y1	0.20
ZD	0.75
ZE	0.75

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R5F100LCAFB, R5F100LDAFB, R5F100LEAFB, R5F100LFAFB, R5F100LGAFB, R5F100LHAFB, R5F100LJAFB,
 R5F100LKAFB, R5F100LLAFB
 R5F101LCAFB, R5F101LDAFB, R5F101LEAFB, R5F101LFAFB, R5F101LGAFB, R5F101LHAFB,
 R5F101LJAFB, R5F101LKAFB, R5F101LLAFB
 R5F100LCDFB, R5F100LDDFB, R5F100LEDDB, R5F100LFDDB, R5F100LGDFB, R5F100LHDFB, R5F100LJDFB,
 R5F100LKDFB, R5F100LLDFB
 R5F101LCDFB, R5F101LDDFB, R5F101LEDDB, R5F101LFDDB, R5F101LGDFB, R5F101LHDFB,
 R5F101LJDFB, R5F101LKDFB, R5F101LLDFB
 R5F100LCGFB, R5F100LDGFB, R5F100LEGFB, R5F100LFGFB, R5F100LGGFB, R5F100LHGFB,
 R5F100LJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP64-10x10-0.50	PLQP0064KF-A	P64GB-50-UEU-2	0.35



NOTE

Each lead centerline is located within 0.08 mm of its true position at maximum material condition.